

## PRODUCT FEATURES

- IGBT<sup>3</sup> CHIP(Trench+Field Stop technology)
- High short circuit capability,self limiting short circuit current
- $V_{CE(sat)}$  with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Low switching losses
- Temperature sense included



## APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems

### IGBT-inverter

ABSOLUTE MAXIMUM RATINGS( $T_C=25^{\circ}C$  unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
$V_{CES}$	Collector Emitter Voltage	$T_J=25^{\circ}C$	600	V
$V_{GES}$	Gate Emitter Voltage		$\pm 20$	
$I_C$	DC Collector Current	$T_C=25^{\circ}C, T_{Jmax}=175^{\circ}C$	125	A
		$T_C=70^{\circ}C, T_{Jmax}=175^{\circ}C$	100	
$I_{CM}$	Repetitive Peak Collector Current	$t_p=1ms$	200	
$P_{tot}$	Power Dissipation Per IGBT	$T_C=25^{\circ}C, T_{Jmax}=175^{\circ}C$	330	W

### Diode-inverter

ABSOLUTE MAXIMUM RATINGS ( $T_C=25^{\circ}C$  unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
$V_{RRM}$	Repetitive Reverse Voltage	$T_J=25^{\circ}C$	600	V
$I_{F(AV)}$	Average Forward Current		100	A
$I_{FRM}$	Repetitive Peak Forward Current	$t_p=1ms$	200	
$I^2t$		$T_J=125^{\circ}C, t=10ms, V_R=0V$	1000	A <sup>2</sup> S

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# MMG100HB060B6EN

## IGBT-inverter

### ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=1.6\text{mA}$	4.9	5.8	6.5	V	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.45	1.9		
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		1.6			
$I_{CES}$	Collector Leakage Current	$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA	
		$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$			5	mA	
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=25^\circ\text{C}$	-400		400	nA	
$R_{gint}$	Integrated Gate Resistor			2		$\Omega$	
$Q_g$	Gate Charge	$V_{CE}=300\text{V}, I_C=100\text{A}, V_{GE}=\pm 15\text{V}$		1.1		$\mu\text{C}$	
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		6.2		nF	
$C_{res}$	Reverse Transfer Capacitance				190		pF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=300\text{V}, I_C=100\text{A}$ $R_G=3.3\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		70		ns
			$T_J=125^\circ\text{C}$		80		ns
$t_r$	Rise Time		$T_J=25^\circ\text{C}$		20		ns
			$T_J=125^\circ\text{C}$		20		ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=300\text{V}, I_C=100\text{A}$ $R_G=3.3\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		260		ns
			$T_J=125^\circ\text{C}$		290		ns
$t_f$	Fall Time		$T_J=25^\circ\text{C}$		70		ns
			$T_J=125^\circ\text{C}$		70		ns
$E_{on}$	Turn on Energy	$V_{CC}=300\text{V}, I_C=100\text{A}$ $R_G=3.3\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		0.3		mJ
			$T_J=125^\circ\text{C}$		0.7		mJ
$E_{off}$	Turn off Energy		$T_J=25^\circ\text{C}$		2.5		mJ
			$T_J=125^\circ\text{C}$		3.35		mJ
$I_{SC}$	Short Circuit Current	$tp_{sc}\leq 6\mu\text{S}, V_{GE}=15\text{V}$ $T_J=125^\circ\text{C}, V_{CC}=360\text{V}$		500		A	
$R_{thJC}$	Junction to Case Thermal Resistance ( Per IGBT )				0.45	K /W	

## Diode-inverter

### ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.55	1.95	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.50		
$t_{rr}$	Reverse Recovery Time	$I_F=100\text{A}, V_R=300\text{V}$		130		ns
$I_{RRM}$	Max. Reverse Recovery Current	$di_F/dt=-5100\text{A}/\mu\text{s}$		150		A
$Q_{RR}$	Reverse Recovery Charge	$T_J=125^\circ\text{C}$		8		$\mu\text{C}$
$E_{rec}$	Reverse Recovery Energy			2.25		mJ
$R_{thJCD}$	Junction to Case Thermal Resistance ( Per Diode )				0.8	K /W

# MMG100HB060B6EN

## NTC CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
$R_{25}$	Resistance $T_C = 25^\circ\text{C}$		5		$\text{K}\Omega$
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$		3375		K

## MODULE CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit	
$T_{Jmax}$	Max. Junction Temperature	175	$^\circ\text{C}$	
$T_{Jop}$	Operating Temperature	-40~150		
$T_{stg}$	Storage Temperature	-40~125		
$V_{isol}$	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
Torque	to heatsink	Recommended (M5)	2.5~5	Nm
	to terminal	Recommended (M6)	3~5	Nm
Weight			200	g

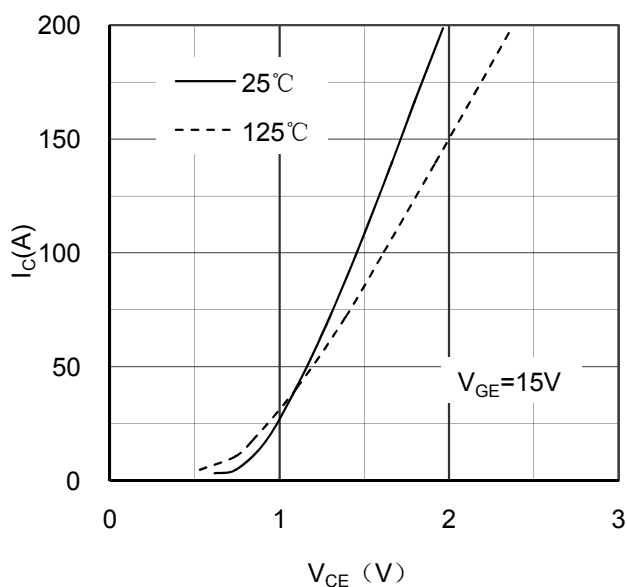


Figure 1. Typical Output Characteristics IGBT-inverter

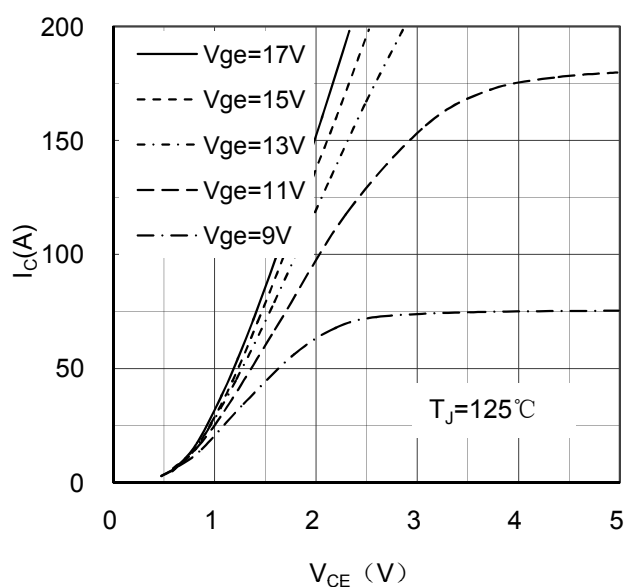


Figure 2. Typical Output Characteristics IGBT-inverter

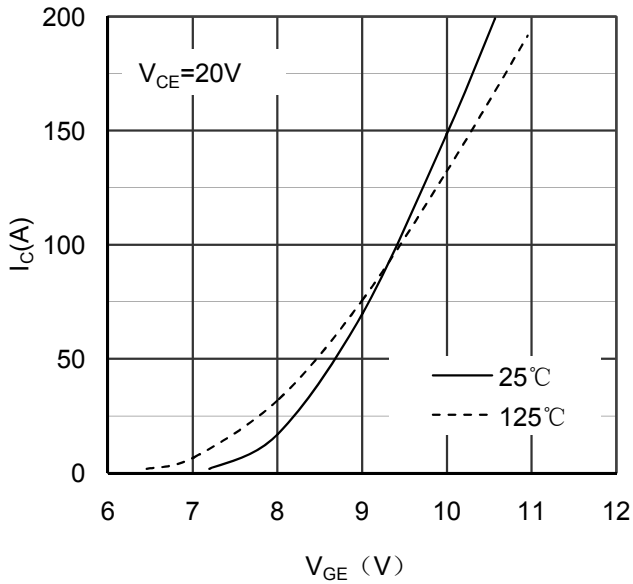


Figure 3. Typical Transfer characteristics IGBT-inverter

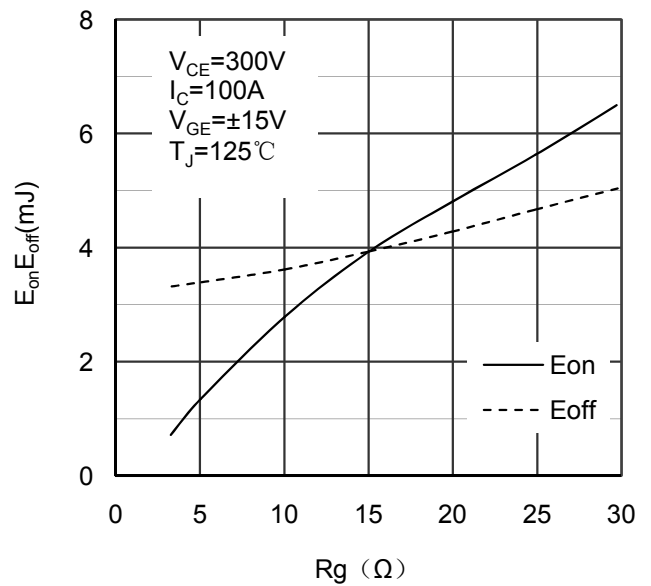


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

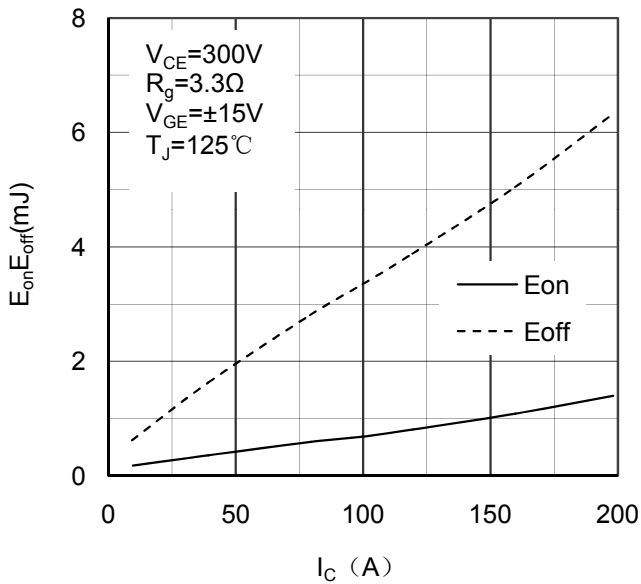


Figure 5. Switching Energy vs Collector Current IGBT-inverter

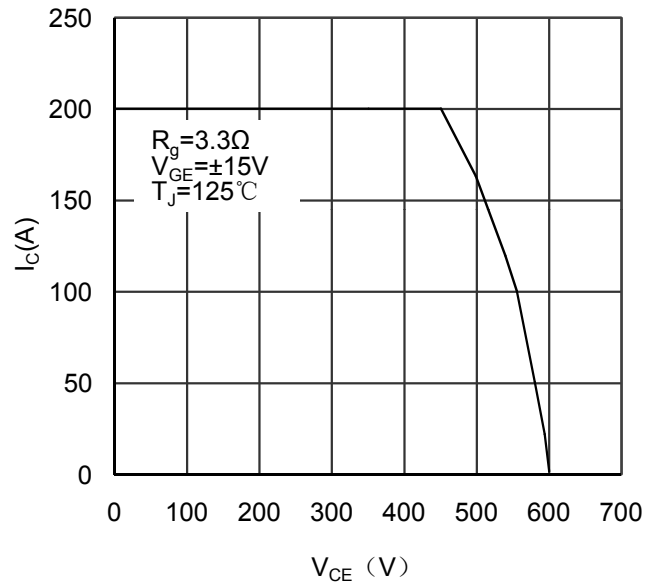


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

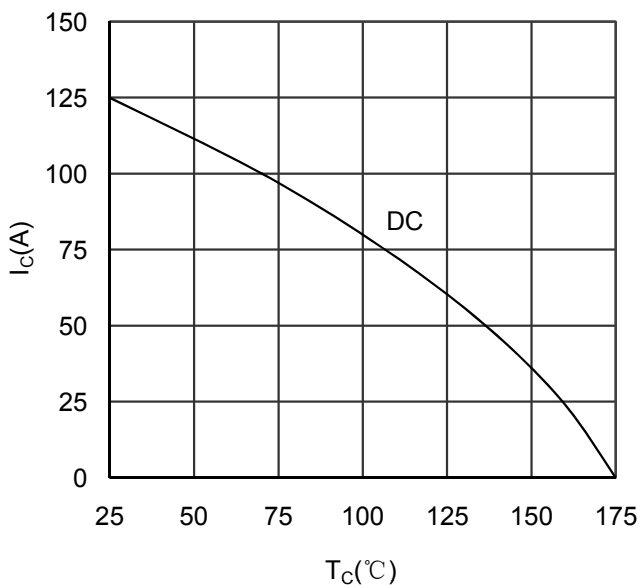


Figure 7. Collector Current vs Case temperature IGBT -inverter

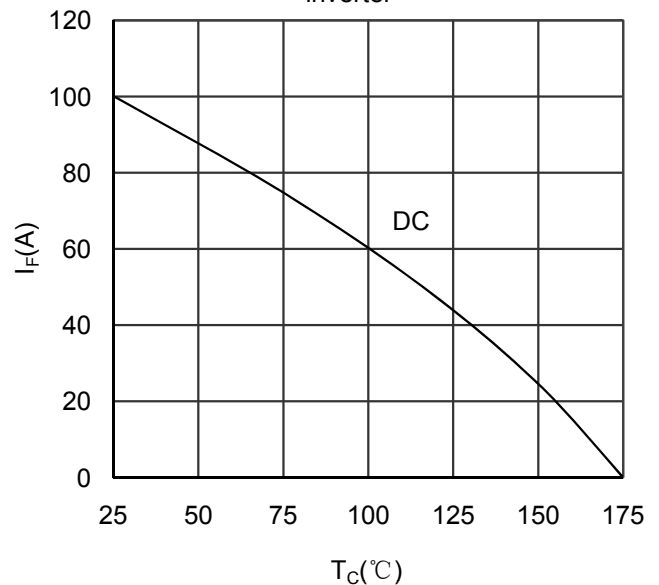


Figure 8. Forward current vs Case temperature Diode -inverter

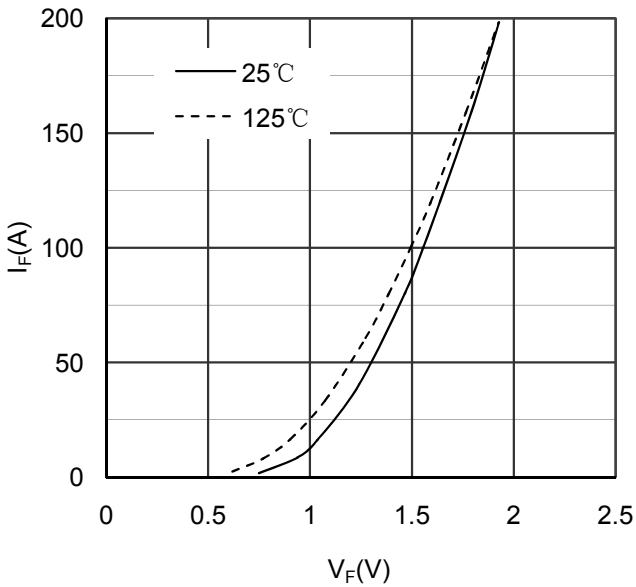


Figure 9. Diode Forward Characteristics Diode-inverter

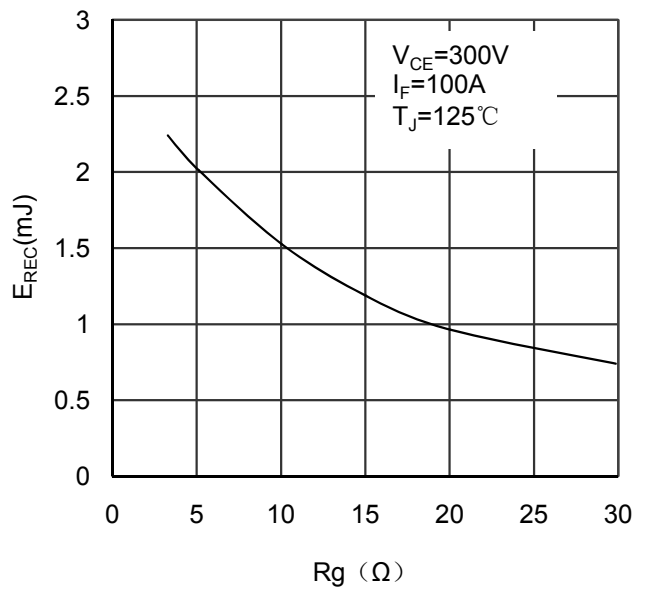


Figure 10. Switching Energy vs Gate Resistor Diode-inverter

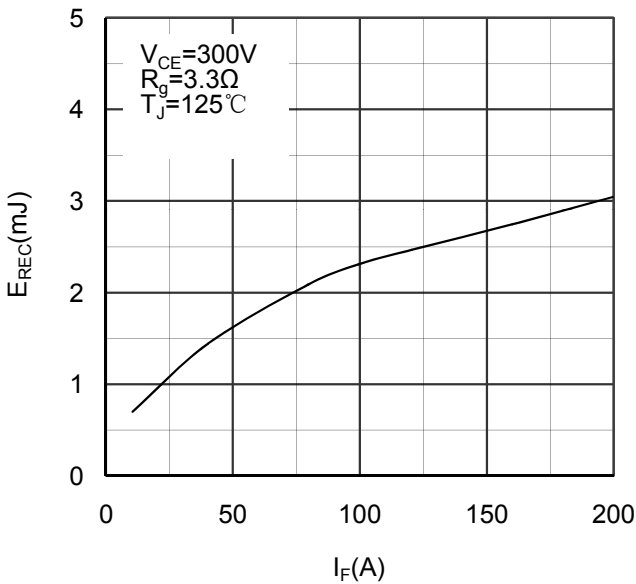


Figure 11. Switching Energy vs Forward Current Diode-inverter

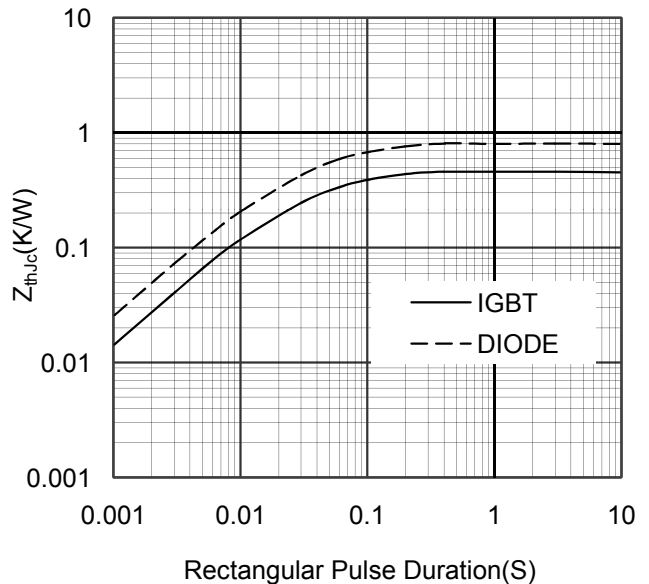


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

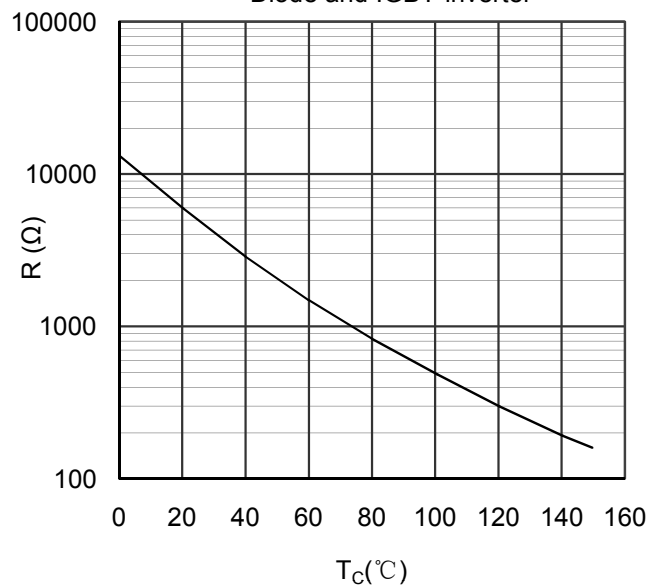


Figure 13. NTC Characteristics

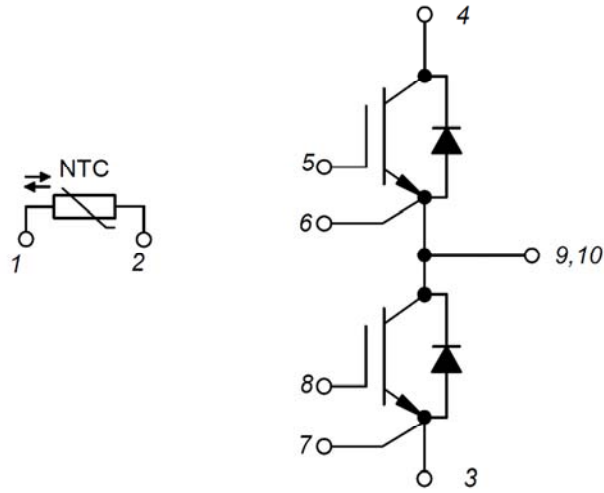
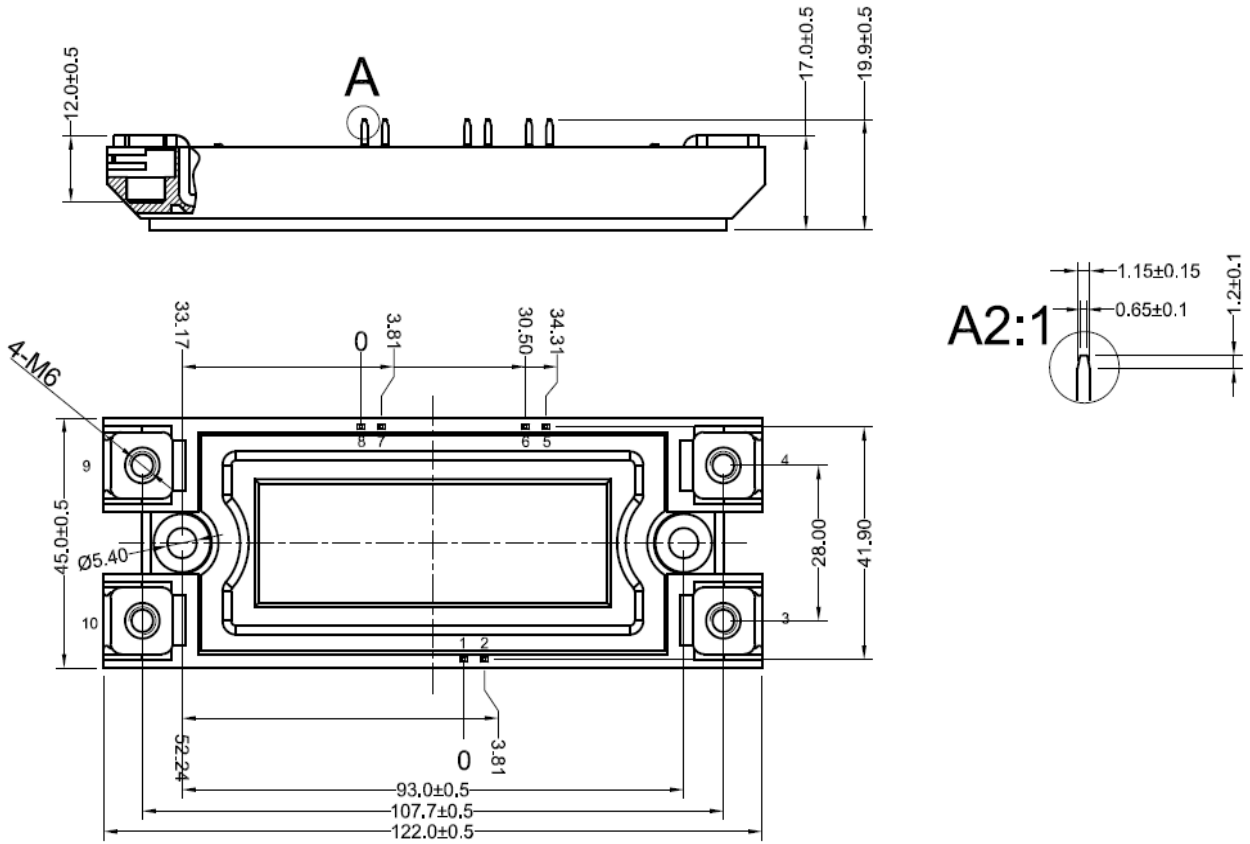


Figure 14. Circuit Diagram



Dimensions in (mm)  
Figure 15. Package Outline